Defect Reactions + RIS Intro

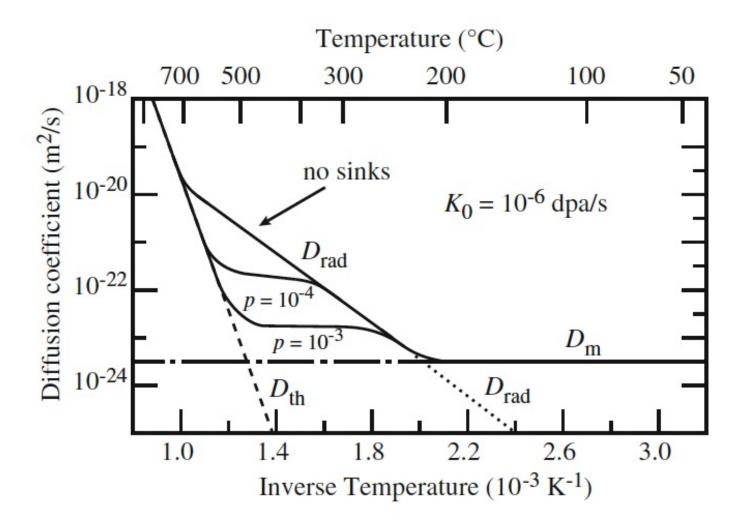
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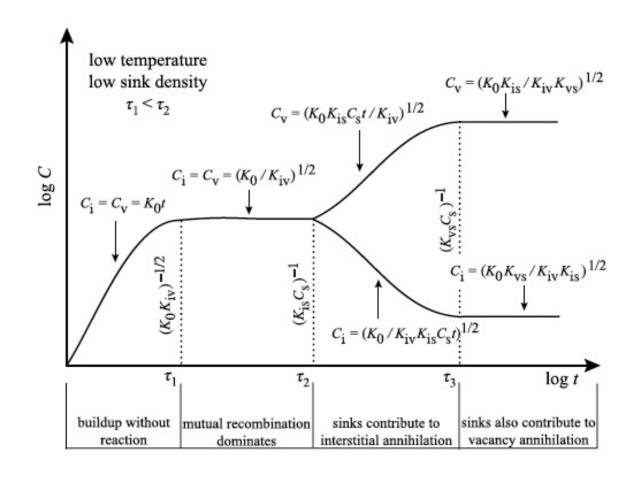


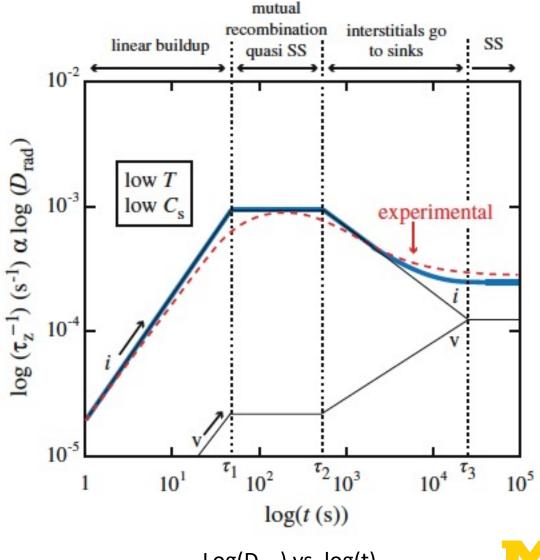
Pulling this now together:





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 $Log(D_{rad})$ vs. log(t)



Rate of Reaction

• We have now determined the relative change of C_i and C_v , but the **rates are dependent on the reaction rate constant** K_{AB} (s⁻¹), where the rate of reaction between A & B is:

$$K_{AB}C_{A}C_{B}$$
 reactions/cm³s

- Analogous to first order chemical reactions
- We will consider two types of reactions:
 - Defect-defect reactions
 - Defect-extended sinks reactions



Point-defect reactions with extended sinks

- To a first approximation, sinks at as "perfect" sinks
- In a perfect sink, all defects "stick" completely to the sink and never leak the sink -> think of these as black holes!
 - Result is the point-defect concentration at the surface of the sink is zero
- The rate of defect absorption at a sink is then:

- The sink strength describes the strength or affinity of a sink for defects and is measured in [length⁻²]. Physically, k_j^{-1} is the mean distance a free defect of type j travels in the solid before becoming trapped.
- For discussion, we will assume unsaturable sinks



Sink types

• Sinks can behave differently:

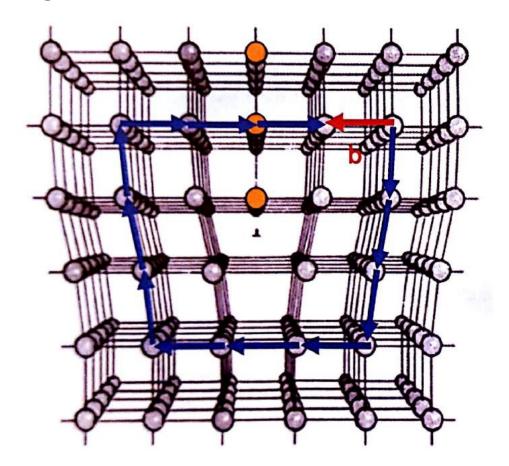
- Neutral sinks:

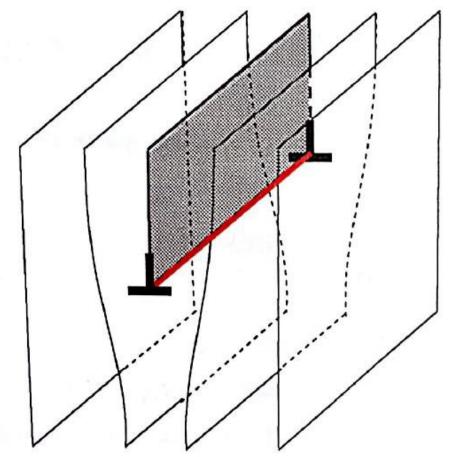
- Biased sinks:

- Variable sinks



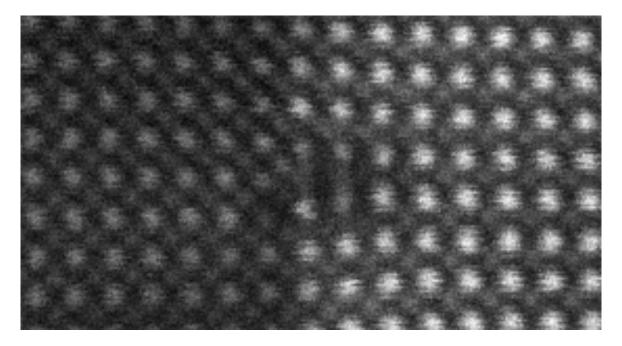
- Linear defect
- Edge dislocation is an additional half plane of atoms
- Burgers vector and slip plane defines dislocation





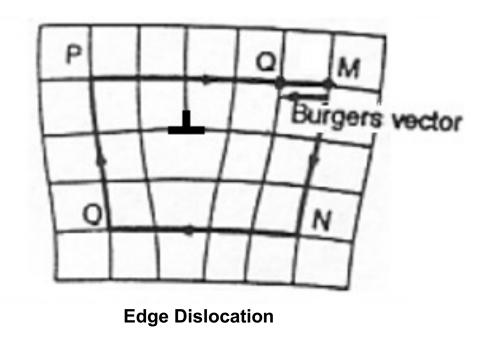


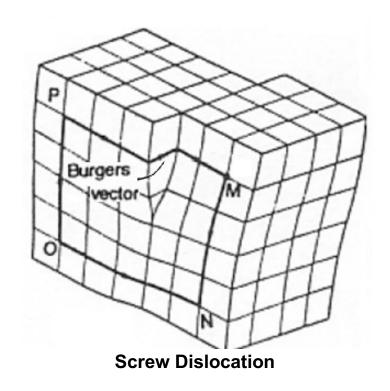
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HAADF STEM Image of dislocation between BaTiO₃ and SrTiO₃



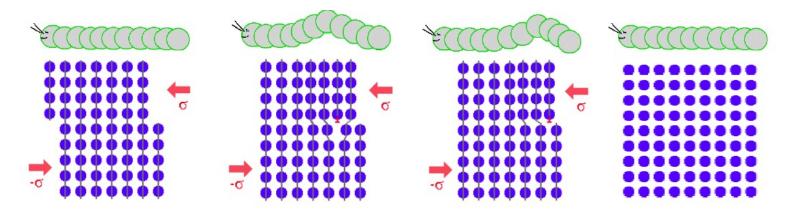




- Three types: Edge, Screw, and Mixed
 - Edge dislocation: line is perpendicular to the Burgers vector
 - Screw dislocation: line is parallel to Burgers vector
 - Mixed dislocations: a combination of edge and screw characterisitics



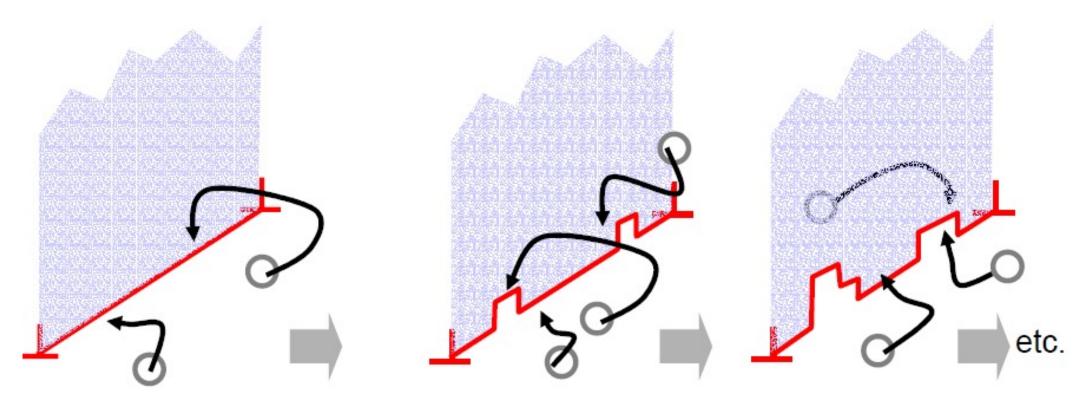
Dislocation motion is the primary form of deformation in a material



- Anything which impedes dislocation motion will strengthen the material, but may make it brittle
 - Defects which impede dislocation motion:
 - Other dislocations
 - Interstitials
 - Impurities
 - Grain boundaries
 - Etc...

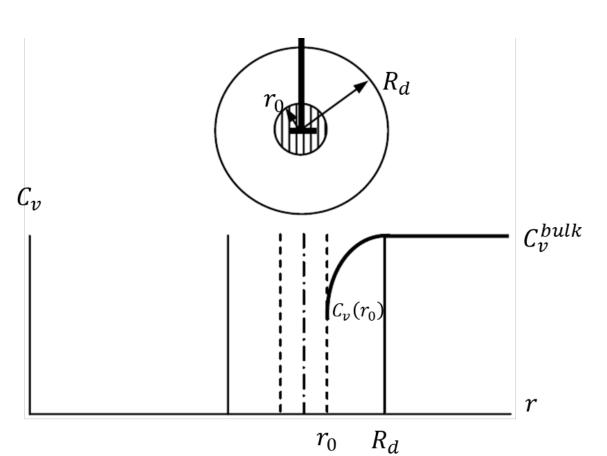


- Dislocation climb by vacancy absorption
- Leads to irradiation glide and creep





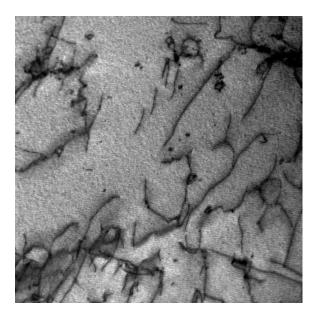
- Net reduction of strain energy
- Absorption leads to jog formation and climb

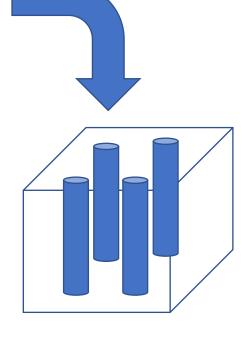


- Assumptions to determine rate of absorption
 - Even distribution of dislocation line density (p_d – cm⁻²)
 - Only one type of dislocation defect
 - Defects enter but do not exit the dislocation core r₀
 - At a distance R_d the concentration of defects is equal to $\mathcal{C}_{i,v}^{bulk}$
 - No influence of the dislocation strain field



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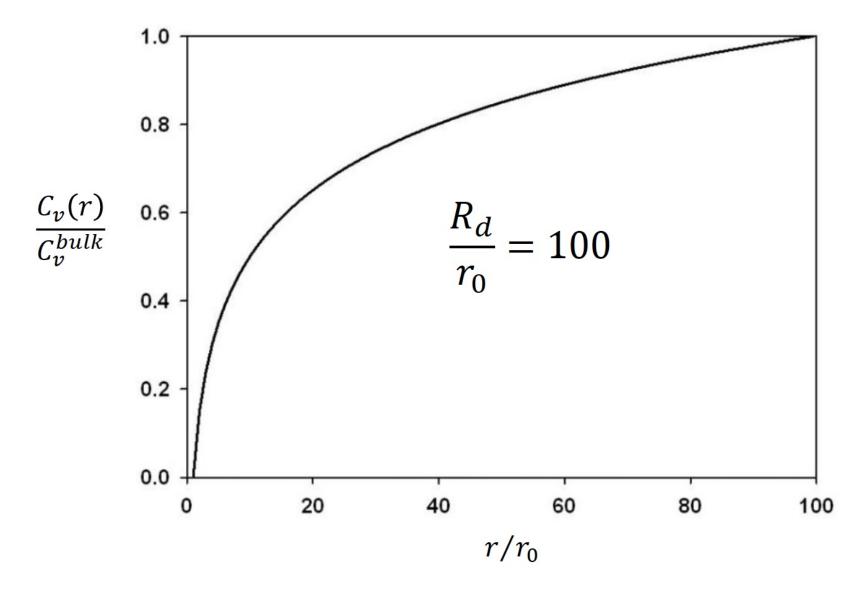
Our steady state assumption gives (in radial coordinates):

The solution is then:

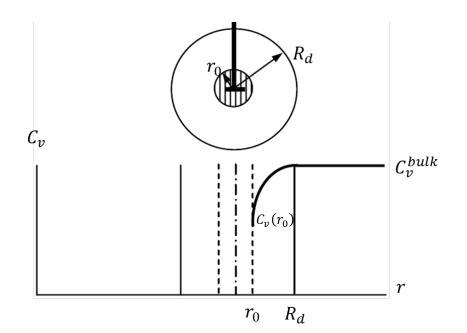
Using the boundary conditions established by our assumptions:

• Gives us:











• We derived:
$$C_{i,v}(r) = C_{i,v}^{bulk} \frac{ln\frac{r}{r_0}}{ln\frac{R_d}{r_0}}$$

and:

$$\frac{dC_{i,v}}{dr} = \frac{C_{i,v}^{bulk}}{\ln\frac{R_d}{r_0}} \frac{1}{r}$$

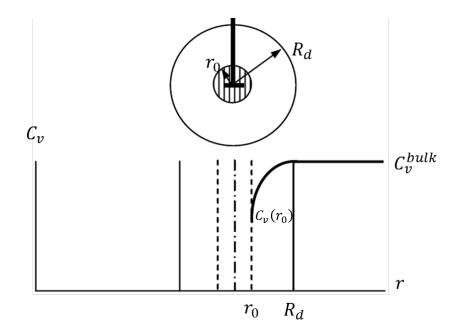
• Rate of absorption per unit length of the dislocation:

• Since there is $\mathbf{p_d}$ cm of dislocation line per cm³:



• For vacancies:

For interstitials:

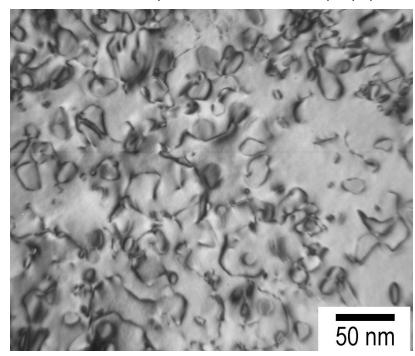


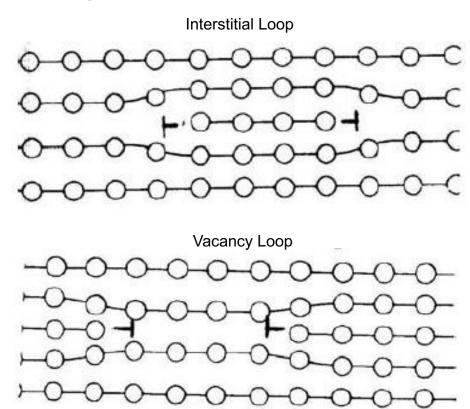
Influence of the dislocation strain field on interstitial is larger (no random walk)



Accounting for dislocation loops

Dislocation Loops in Irradiated 316 SS (2 dpa)





- Dislocation Loop: when a dislocation line forms a closed loop instead of extending until it reaches an interface
 - Character of the dislocation (edge, screw, mixed) changes continuously along the line
 - Loops typically grow



Accounting for dislocation loops

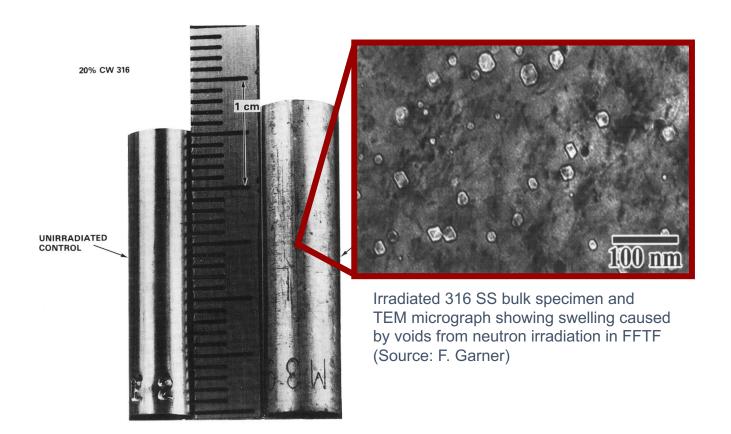
 We derived the reaction rate and sink strength for dislocation lines, but it is also used for dislocation loops. For loops p_d is used but with no consideration of geometry, e.g. the circular dislocation loops are effectively "straightened out"



Sink types

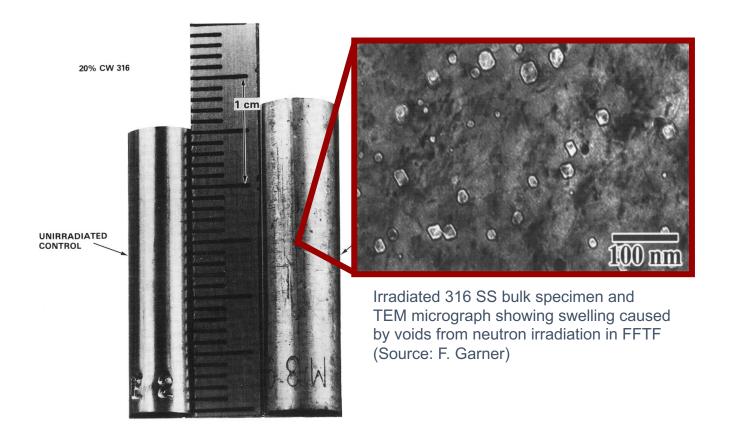
- Sinks can behave differently:
 - Neutral sinks: Neutral sinks show no preference for capturing one type of defect over another. Examples are voids and grain boundaries.
 - Biased sinks: Biased sinks show a preferential attraction for one defect over another. Examples are network dislocations.
 - Variable sinks: Variable sinks act as traps for defects which hold the defect but preserve its identity until annihilation or it is released. Examples are coherent precipitates.





- Cavities are due to vacancies (and possibly gas atoms) diffusing and coalescing together within the matrix
- Can lead to brittle fracture (bad!)

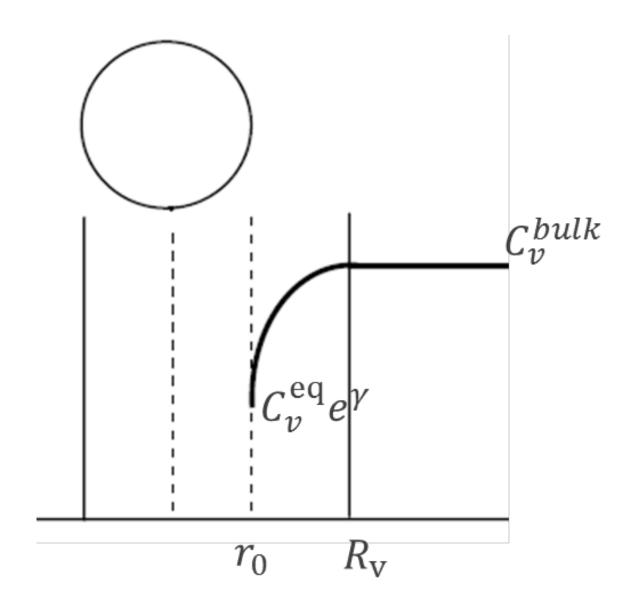




• Similar arguments for point defect absorption can be made in the case of voids:

$$\frac{1}{r^2}\frac{d}{dr}\left(r^2\frac{dC_v}{dr}\right) = 0 \qquad \to C_v(r) = -\frac{A}{r} + B$$

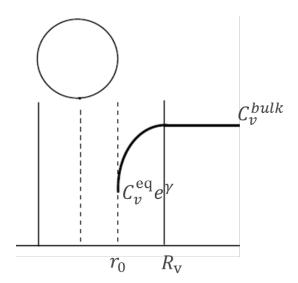




It is assumed that the boundary conditions are:

In these conditions:









Point Defect Kinetic Equations

If we neglect clustering:

$$\frac{\partial C_v}{\partial t} = K_0 - K_{iv}C_iC_v - \sum_S K_{vs}C_vC_s + D_v\nabla^2C_v$$

$$\frac{\partial C_i}{\partial t} = K_0 - K_{iv}C_iC_v - \sum_{S} K_{is}C_vC_S + D_i\nabla^2C_i$$

Example of defect absorption to cavities:

$$\frac{\partial C_v}{\partial t} = K_0 - K_{iv}C_iC_v - z_v p_d D_v C_v + 4\pi R_c N_c D_v C_v$$

$$\frac{\partial C_i}{\partial t} = K_0 - K_{iv}C_iC_v - z_v p_d D_iC_i + 4\pi R_c N_c D_iC_i$$

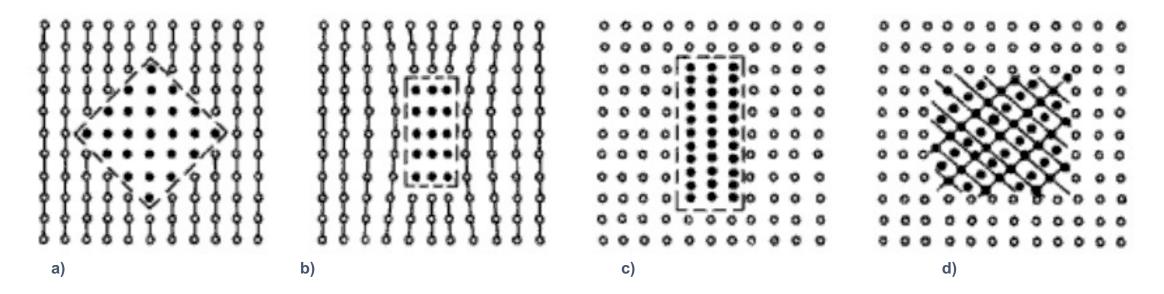


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Sink Type III – Coherent Precipitates (PPTs)



- Precipitates are the result of the local solubility limit being reached causing a new phase to form
- Precipitates can be either coherent, partially coherent or incoherent
 - Coherency: a perfect lattice match between the PPT and matrix
 - Coherency affects how dislocations interact with the PPT
 - Coherency can also affect diffusion in and around the PPT



Sink Type III – Coherent Precipitates (PPTs)



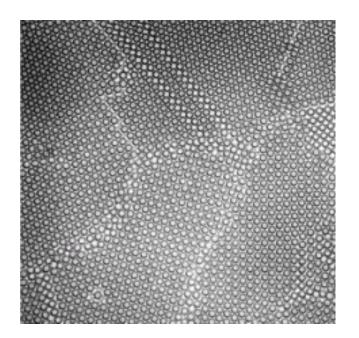
- Precipitates impede dislocation motion
- Inclusion of precipitates can strengthen a material



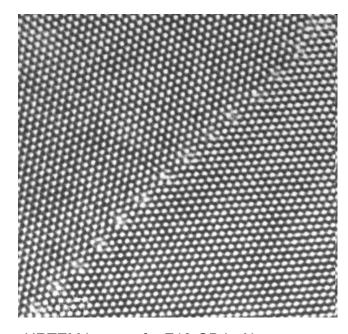
Sink Type III – Coherent Precipitates (PPTs)



Sink Type IV – Grain Boundaries





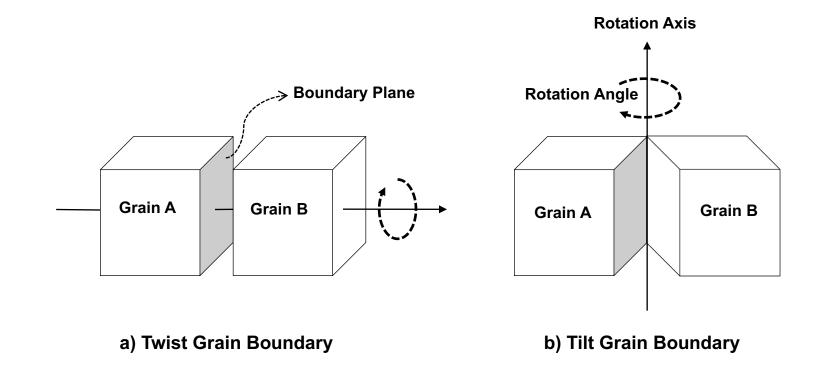


HRTEM image of a Σ19 GB in Al

- A Grain Boundary is a general planar defect that separates regions of different crystalline orientation (i.e. grains) within a polycrystalline solid
- Grain boundaries can affect creep strength, yield strength, and diffusion



Sink Type IV – Grain Boundaries



- Grain boundaries can have twist, tilt, or mixed character
- Variations in the degree of misalignment between two adjacent grains are possible

